CA-IS1306x 5kV$_{RMS}$ Isolated Sigma-Delta Modulator

1 Key Features

- Full-Scale Sense Voltage Range: ±250 mV
- Uncoded Bitstream Output
- Ultra-Low Input Offset Voltage and Gain Error
  - ±100 µV (max) at 25°C input offset voltage
  - ±0.2% (max) at 25°C gain error
- Low Drift
  - ±3.5 µV/°C (max) input offset tempco
  - ±40 ppm/°C (max) gain drift
- Excellent AC Performance
  - SNR: 85dB (typ)
  - THD: -93dB (typ)
- 16-Bit Resolution with No Missing Codes
- Wide Power Supply Operating Range
  - 3.3V to 5.5V supply range for both high-side and low-side
- Robust Isolation Barrier
  - High lifetime: >40 years
  - Up to 5000 V_{RMS} isolation rating
  - ±150 kV/µs typical CMTI
- Fault Diagnostic Functions Improve System Safety
- Wide Operating Temperature Range: –40°C to 125°C
- Safety Regulatory Approvals
  - VDE 0884-17 isolation certification
  - UL according to UL1577
  - IEC 61010-1:2010+A1 certifications

2 Applications

- Industrial Motor Controls and Drives
- Isolated Power Supplies
- Process Signal Isolation

3 General Description

The CA-IS1306x family of devices is series of precision isolated sigma-delta (Σ-Δ) modulator and optimized for shunt resistor-based current sensing or other small signal measurement applications. The input current-sense amplifier monitors current flow through a shunt (sense) resistor and the sigma-delta modulator converts the analog input to a digital bit stream of 1's and 0's at a much higher frequency.

The analog input-side (high-side) and digital output-side (low-side) are separated by unique silicon oxide (SiO_2) capacitive isolation barriers that provide up to 5kV$_{RMS}$ galvanic isolation per UL1577 certification, and isolator drivers transfer the output of the modulator across this isolation barrier. In systems with different voltage domains, this isolation technical is typically used to protect the low voltage side from the high voltage side in case of any faults. These devices also feature up to 150kV/µs common mode transient immunity and enable efficient bit-stream transmission in noisy environments.

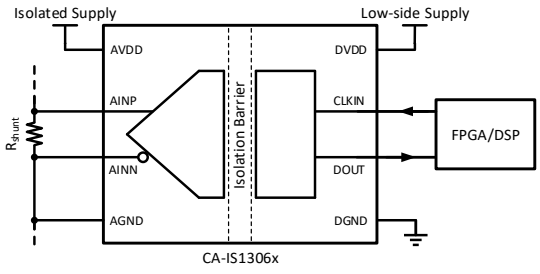
The CA-IS1306x devices' ultra-low input voltage range (±250mV) allows the use of small sense resistor to reduce power dissipation and a very low, 0.2% gain error ensures measurement accuracy. This family of devices also features fail-safe output to support high safety system design. The CA-IS1306x devices specified for operation with 5MHz to 21MHz clock input. The internal sigma-delta modulator combined with an external digital decimation sinc^3 filter can achieve 85 dB signal-to-noise ratio (SNR) at 78.1 Ksps.

The CA-IS1306x family is specified over the -40°C to +125°C operating temperature range and is available in 8-pin SOIC wide body package.

Device Information

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CA-IS1306x	SOIC8-WB (G)	5.85 mm × 7.50 mm
CA-IS1306AMx	SOIC16-WB (W)	10.3 mm × 7.50 mm
CA-IS1306M25W	SOIC16-WB (W)	10.3 mm × 7.50 mm

Simplified Schematic



4 Ordering Information

Table 4-1. Ordering Information

Ordering Part Number	Specified Input Range	Galvanic Isolation (±V)	Package	Digital Output Encoded Mode
CA-IS1306M25G	±250 mV	5000 V_{RMS}	SOIC8-WB(G)	Uncoded CMOS
CA-IS1306AM25W	±250 mV	5000 V_{RMS}	SOIC16-WB(W)	Uncoded CMOS
CA-IS1306M25W	±250 mV	5000 V_{RMS}	SOIC16-WB(W)	Uncoded CMOS

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5 Revision History

Revision Number	Description	Page Changed
Version 1.00	Revised the CA-IS1306M25 specs. Added typical characteristics and waveforms.	7~9 10~13
Version 1.01	Add CA-IS1306AM25 part number and package information. Updated CMRR, PSRR data; Updated I_{DVDD} data and some typical curves; Updated INL,DNL,CMRR and PSRR curves.	5, 26 9 10, 16 17
Version 1.02	Added CA-IS1306M25W part number and PIN descriptions	1, 2, 6, 29
Version 1.03	Removed part number CA-IS1306E25G	29
Version 1.04	Updated UL certification	9
Version 1.05	Updated TUV and VDE certification	8~9
Version 1.06	Updated TUV and UL certification	9

6 Pin Configuration and Description

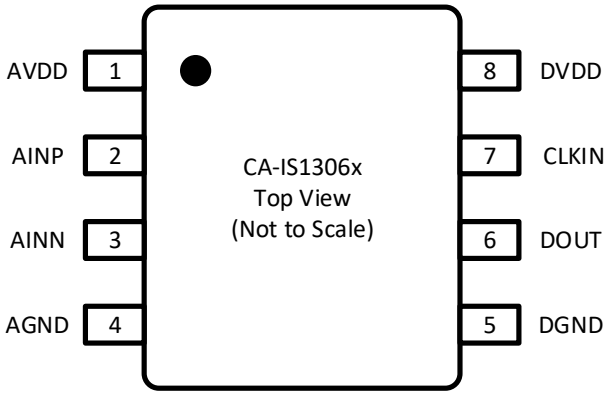


Figure 6-1. CA-IS1306x Top View

Table 6-1. CA-IS1306x Pin Configuration and Description

NAME	Pin #	TYPE	DESCRIPTION
AVDD	1	Power	Power supply input for the input-side (analog input-side), 3.0V to 5.5V. Bypass AVDD to AGND with 0.1μF //2.2μF capacitors as close to the device as possible.
AINP	2	Input	Noninverting analog input. External shunt resistor connection input (power-side) for current sense.
AINN	3	Input	Inverting analog input. External shunt resistor connection input (load-side) for current sense.
AGND	4	Ground	High-side (input-side) ground.
DGND	5	Ground	Low-side (output-side) ground.
DOUT	6	Output	Modulator bit-stream output.
CLKIN	7	Output	Modulator clock input(5 MHz to 21 MHz) with internal 1.5-MΩ pulldown resistor.
DVDD	8	Power	Low-side (digital output-side) power supply, 3.0V to 5.5V. Bypass DVDD to DGND with 0.1μF //2.2μF capacitors as close to the device as possible.

6.1 CA-IS1306AM25W

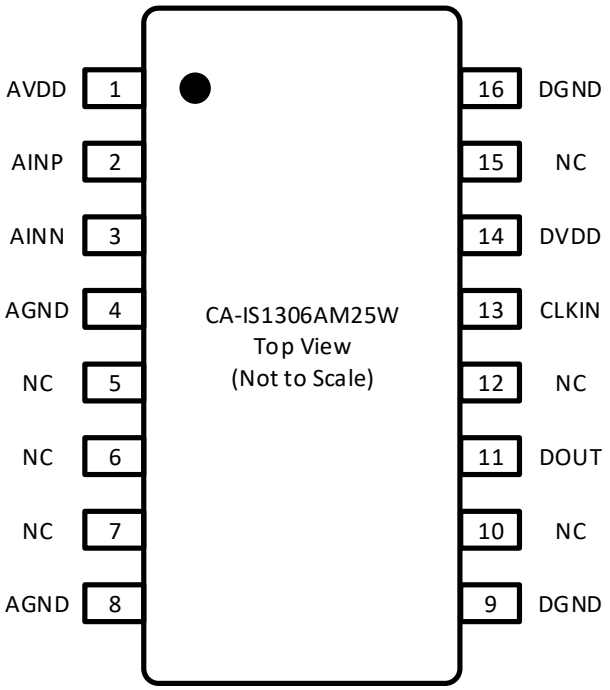


Figure 6- 2 CA-IS1306AM25W Top View

Table 6- 2 CA-IS1306AM25W Pin description

NAME	Pin #	TYPE	DESCRIPTION
AVDD	1	Power	Power supply input for the input-side (analog input-side), 3.0V to 5.5V. Bypass AVDD to AGND with 0.1μF //2.2μF capacitors as close to the device as possible.
AINP	2	Input	Noninverting analog input. External shunt resistor connection input (power-side) for current sense.
AINN	3	Input	Inverting analog input. External shunt resistor connection input (load-side) for current sense.
AGND	4, 8	Ground	High-side (input-side) ground.
DGND	9, 16	Ground	Low-side (output-side) ground.
DOUT	11	Output	Modulator bit-stream output.
CLKIN	13	Input	Modulator clock input(5 MHz to 21 MHz) with internal 1.5-MΩ pulldown resistor.
DVDD	14	Power	Low-side (digital output-side) power supply, 3.0V to 5.5V. Bypass DVDD to DGND with 0.1μF //2.2μF capacitors as close to the device as possible.
NC	5, 6, 7	–	No connection. Left floating or connect to AVDD or AGND.
	10, 12, 15	–	No connection. Left floating or connect to DVDD or DGND

6.2 CA-IS1306M25W

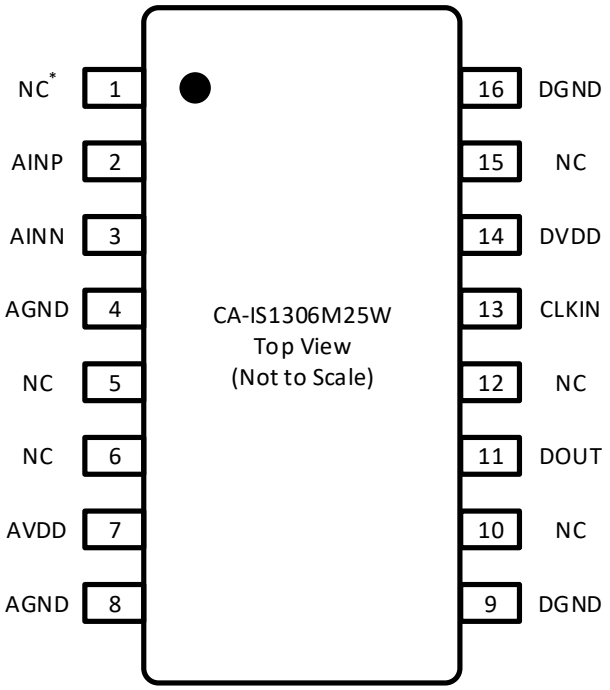


Figure 6- 3 CA-IS1306M25W Top View

Figure 6- 1 CA-IS1306M25W Pin description

引脚名称	引脚编号	引脚类型	描述
AVDD	7	Power	Power supply input for the input-side (analog input-side), 3.0V to 5.5V. Bypass AVDD to AGND with 0.1μF //2.2μF capacitors as close to the device as possible.
AINP	2	Input	Noninverting analog input. External shunt resistor connection input (power-side) for current sense.
AINN	3	Input	Inverting analog input. External shunt resistor connection input (load-side) for current sense.
AGND	4, 8	Ground	High-side (input-side) ground.
DGND	9, 16	Ground	Low-side (output-side) ground.
DOUT	11	Output	Low-side (output-side) ground.
CLKIN	13	Intput	Modulator bit-stream output.
DVDD	14	Power	Low-side (digital output-side) power supply, 3.0V to 5.5V. Bypass DVDD to DGND with 0.1μF //2.2μF capacitors as close to the device as possible.
NC	1*	–	Internally connected to AVDD,Connect this pin to AVDD or left floating.
	5, 6	–	No connection. Left floating or connect to AVDD or AGND.
	10, 12, 15	–	No connection. Left floating or connect to DVDD or DGND

7 Specifications

7.1 Absolute Maximum Ratings[1]

PARAMETER		MIN	MAX	UNIT
AVDD, DVDD	Supply voltage[2]	–0.5	6.5	V
AINP, AINN	Analog input voltage	AGND – 6	6.5	V
CLKIN, DOUT	Digital input or output voltage	DGND – 0.5	DVDD + 0.5[3]	V
I_{IN}	Input current to any pin except supply pins	–10	10	mA
T_J	Junction Temperature		150	°C
T_{STG}	Storage Temperature	–65	150	°C

Notes:

1. The stresses listed under "Absolute Maximum Ratings" are stress ratings only, not for functional operation condition. Exposure to absolute maximum rating conditions for extended periods may cause permanent damage to the device.
1. All voltage values are with respect to the local ground terminal (AGND or DGND) and are peak voltage values.
2. Maximum voltage must not exceed 6.5V.

7.2 ESD Ratings

		VALUE	UNIT
V_{ESD} Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins[1]	±4000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins[2]	±2000	

Notes:

1. Per JEDEC document JEP155, 500V HBM allows safe manufacturing of standard ESD control process.
2. Per JEDEC document JEP157, 250V CDM allows safe manufacturing of standard ESD control process.

7.3 Recommended Operating Conditions

PARAMETER		MIN	NOM	MAX	UNIT
AVDD	High-side (analog input) supply voltage, with respect to AGND	3.0	5.0	5.5	V
DVDD	Low-side (digital output) supply voltage, with respect to DGND	3.0	3.3	5.5	V
T_A	Operating ambient temperature range	–40		125	°C
AINP – AINN	Differential analog input range	-250		+250	mV

7.4 Thermal Information

THERMAL METRIC		VALUE	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	110.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	51.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	66.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter	16.0	°C/W
ψ_{JB}	Junction-to-board characterization parameter	64.5	°C/W
$R_{\theta JC(bottom)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

7.5 Power Ratings

PARAMETER		TEST CONDITIONS	VALUE	UNIT
P_D	Maximum power dissipation for both sides	CA-IS1306Mx, AVDD = DVDD = 5.5 V	129.25	mW
P_{D1}	Maximum power dissipation for high-side	AVDD = 5.5 V	90.75	mW
P_{D2}	Maximum power dissipation for low-side	CA-IS1306Mx, DVDD = 5.5 V	38.50	mW

7.6 Insulation Specifications

PARAMETR		TEST CONDITIONS	VALUE	UNIT
CLR	External clearance [1]	Shortest terminal-to-terminal distance through air	8	mm
CPG	External creepage [1]	Shortest terminal-to-terminal distance across the package surface	8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	28	µm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	> 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 300 V_{RMS}	I-IV	
		Rated mains voltage ≤ 600 V_{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V_{RMS}	I-III	
DIN V VDE V 0884-17:2021-10				
V_{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1414	V_{PK}
V_{IOWM}	Maximum working isolation voltage	AC voltage; Time dependent dielectric breakdown (TDDB) Test	1000	V_{RMS}
		DC voltage	1414	V_{DC}
V_{IOTM}	Maximum transient isolation voltage	$V_{TEST} = V_{IOTM}$, t = 60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$, t= 1 s (100% production)	7070	V_{PK}
V_{IOSM}	Maximum surge isolation voltage[2]	Test method per IEC 62368-1, 1.2/50 µs waveform, $V_{TEST} = 1.6 \times V_{IOSM}$ (qualification)	8000	V_{PK}
q_{pd}	Apparent charge[3]	Method a, After input/output safety test subgroup 2/3, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.2 \times V_{IORM}$, t_m = 10 s	≤ 5	pC
		Method a, After environmental tests subgroup 1, $V_{ini} = V_{IOTM}$, t_{ini} = 60 s; $V_{pd(m)} = 1.6 \times V_{IORM}$, t_m = 10 s	≤ 5	
		Method b1, At routine test (100% production) and preconditioning (type test) $V_{ini} = 1.2 \times V_{IOTM}$, t_{ini} = 1 s; $V_{pd(m)} = 1.875 \times V_{IORM}$, t_m = 1 s	≤ 5	
C_{IO}	Barrier capacitance, input to output[4]	V_{IO} = 0.4 × sin (2πft), f = 1 MHz	~ 1	pF
R_{IO}	Isolation resistance[4]	V_{IO} = 500 V, T_A = 25°C	> 10^{12}	Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ 125°C	> 10^{11}	
		V_{IO} = 500 V at T_S = 150°C	> 10^9	
	Pollution degree		2	
UL 1577				
V_{ISO}	Maximum withstanding isolation voltage	$V_{TEST} = V_{ISO}$, t = 60s (qualification), $V_{TEST} = 1.2 \times V_{ISO}$, t = 1s (100% production)	5000	V_{RMS}

Notes:

1. This coupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
2. Devices are immersed in oil during surge characterization.
3. The characterization charge is discharging charge (pd) caused by partial discharge.
4. Capacitance and resistance are measured with all pins on high-side and low-side tied together.

7.7 Safety-Related Certifications

VDE	UL	CQC	TUV
Certified according to DIN EN IEC 60747-17 (VDE 0884-17):2021-10; EN IEC 60747-17:2020+AC:2021	Recognized under UL 1577 Component Recognition Program	Certified according to GB 4943.1-2022	Certified according to EN 61010-1:2010+A1
Maximum transient isolation voltage：7070V_{pk}(SOIC16-WB) and 7070V_{pk}(SOIC8-WB) Maximum repetitive peak isolation voltage： 1414V_{pk}(SOIC16-WB) and 1414V_{pk}(SOIC8-WB) Maximum surge isolation voltage： 8000V_{pk}(SOIC16-WB) and 8000V_{pk}(SOIC8-WB)	SOIC8-WB:5000V_{RMS} SOIC16-WB:5000V_{RMS}	SOIC8-WB: Reinforced insulation SOIC16-WB: Reinforced insulation （Altitude ≤ 5000 m）	SOIC8-WB:5000V_{RMS} SOIC16-WB:5000V_{RMS}
Certification number: 40057278（CA-IS1306AM25W under certification)	Certification number:E511334	Certificate number: SOIC16-WB:CQC23001406424 SOIC8-WB:CQC24001434134	Certification number: AK 505918190001

7.8 Electrical Characteristics

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
$V_{Clipping}$	Maximum input voltage before clipping output	AINP – AINN		±320		mV
V_{FSR}	Specified linear full-scale input range	AINP – AINN	–250		250	mV
V_{CM}	Operating common-mode input voltage	(AINP + AINN) / 2 to AGND	–0.16		AVDD – 2.1	V
V_{CMOV}	Common-mode overvoltage threshold	(AINP + AINN) / 2 to AGND	AVDD – 2			V
V_{CMOV_HYS}	Hysteresis of common-mode over-voltage threshold			100		mV
C_{IN}	Single-ended input capacitance	f_{IN} = 270 kHz, AINN = AGND		2		pF
C_{IND}	Differential input capacitance	f_{IN} = 270 kHz		1		pF
R_{IN}	Single-ended input resistance	AINN = AGND		19		kΩ
R_{IND}	Differential input resistance			22		kΩ
I_{IN}	Input current	AINP = AINN = AGND, $I_{IN} = (I_{INP} + I_{INN}) / 2$	–41	–30	–24	µA
TCI_{IN}	Input current drift			±1		nA/°C
I_{INOS}	Input offset current	$I_{INOS} = I_{INP} – I_{INN}$		±5		nA
$CMRR_{IN}$	Input common-mode rejection ratio	DC, AINP = AINN		–85		dB
		f_{IN} = 10 kHz, AINP = AINN		–85		
PSRR	Power supply rejection ratio	At AVDD, DC, AINP = AINN = AGND		–98		dB
		At AVDD, 100-mV and 10-kHz ripple, AINP = AINN = AGND		–98		
BW_{IN}	–3 dB input bandwidth			1000		kHz
CMTI	Common-mode transient immunity	|AGND – DGND| = 1.5 kV	100	150		kV/µs
MODULATOR ACCURACY						
DNL	Differential nonlinearity	Resolution: 16 bits	–0.99		0.99	LSB
INL	Integral nonlinearity[1]	Resolution: 16 bits	–6	±2	6	LSB
E_O	Offset error	Initial, at T_A = 25°C, AINP = AINN = AGND	–100	±4.5	100	µV
TCE_O	Offset drift		–3.5	±0.5	3.5	µV/°C
E_G	Gain error	Initial, at T_A = 25°C	–0.2%	±0.05%	0.2%	
TCE_G	Gain drift		–40	±20	40	ppm/°C
SNR	Signal-to-noise ratio	f_{IN} = 1 kHz, BW = 10 kHz		85		dB
SINAD	Signal-to-noise-and-distortion ratio	f_{IN} = 1 kHz, BW = 10 kHz		84		dB
THD	Total harmonic distortion	f_{IN} = 1 kHz, BW = 10 kHz		–93		dB
SFDR	Spurious-free dynamic range	f_{IN} = 1 kHz, BW = 10 kHz		94		dB

Note:

1. The INL is defined as the maximum deviation from a straight line passing through the end-point of the ideal ADC transfer function once the gain and offset errors have been nullified and expressed as number of LSBs over the specified linear full-scale input range.

Electrical Characteristics (Continued)

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DIGITAL INPUT						
I_{IN}	Input current	DGND ≤ V_{IN} ≤ DVDD	0		7	µA
C_{IN}	Input capacitance			4		pF
V_{IH}	Logic high-level input voltage		0.7 × DVDD		DVDD + 0.3	V
V_{IL}	Logic low-level input voltage		-0.3		0.3 × DVDD	V
DIGITAL OUTPUT						
C_L	Output load capacitance			30		pF
V_{OH}	Logic high-level output voltage	I_{OH} = –20 µA	DVDD – 0.1			V
		I_{OH} = –4 mA	DVDD – 0.4			
V_{OL}	Logic low-level output voltage	I_{OL} = 20 µA			0.1	V
		I_{OL} = 4 mA			0.4	
POWER SUPPLY						
$AVDD_{UV}$	AVDD undervoltage threshold	AVDD rising		2.5	2.7	V
I_{AVDD}	High-side supply current	3.0 V ≤ AVDD ≤ 3.6 V		10.5	15.0	mA
		4.5 V ≤ AVDD ≤ 5.5 V		11.5	16.5	
I_{DVDD} Low-side supply current with C_L = 15 pF[1]		CA-IS1306M25, 3.0 V ≤ DVDD ≤ 3.6 V		3.3	5.3	mA
		CA-IS1306M25, 4.5 V ≤ DVDD ≤ 5.5 V		4.0	7.0	

Note:
1. C_L is approximately 15pF including external (probe and stray) capacitance.

7.9 Switching Characteristics

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{CLKIN}	CLKIN clock frequency	4.5 V ≤ AVDD ≤ 5.5 V	5		21	MHz
		3.0 V ≤ AVDD ≤ 5.5 V	5		20	
Duty Cycle	CLKIN clock duty cycle	t_{HIGH} / t_{CLKIN}, 3.0 V ≤ AVDD ≤ 5.5 V	45%	50%	55%	
		t_{HIGH} / t_{CLKIN}, 4.5 V ≤ AVDD ≤ 5.5 V	42.5%	50%	57.5%	
t_h	Hold time of DOUT after rising edge of CLKIN[1]	C_L = 15 pF [2]; *See Figure*	3.5			ns
t_d	Delay time of DOUT after rising edge of CLKIN[1]	C_L = 15 pF [2]; *See Figure*			16	ns
t_r	Rise time of DOUT (10%–90%)	C_L = 15 pF [2]		1.8	5.0	ns
t_f	Fall time of DOUT (90%–10%)	C_L = 15 pF [2]		1.8	5.0	ns
t_{astart}	Analog startup time	AVDD step to 3.0 V with 2.7 V ≤ DVDD; *See Figure*		500		µs

Notes:
1. C_L is approximately 15pF including external (probe and stray) capacitance.

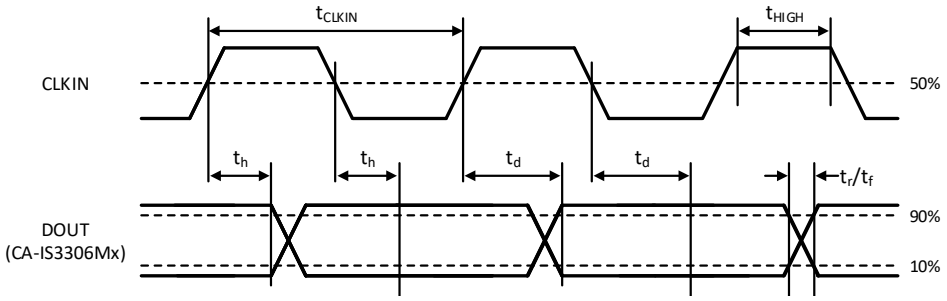


Figure 7-1. CA-IS1306x Digital Output Timing

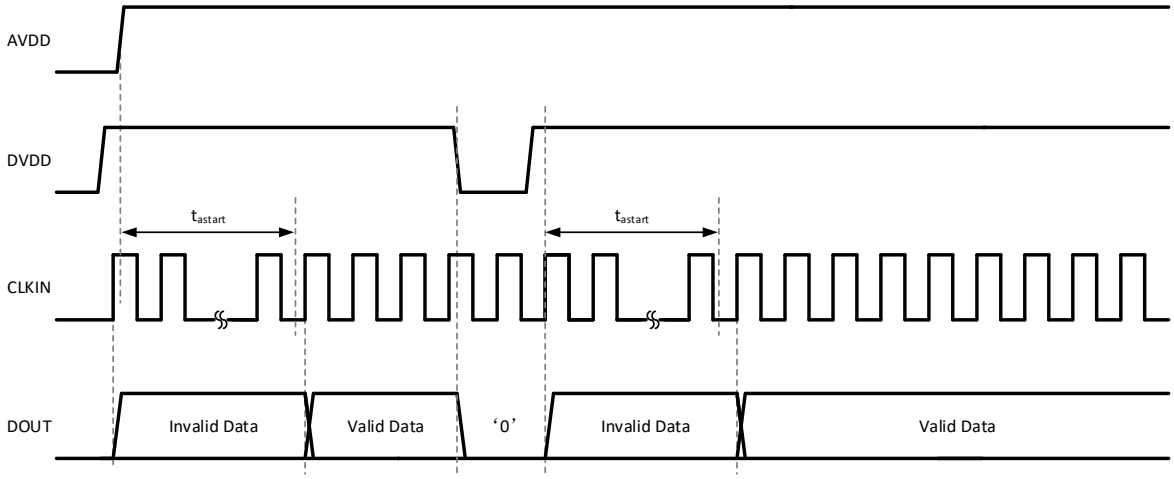


Figure 7-2. CA-IS1306x Startup Timing

7.10 Typical Characteristics and Waveforms

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

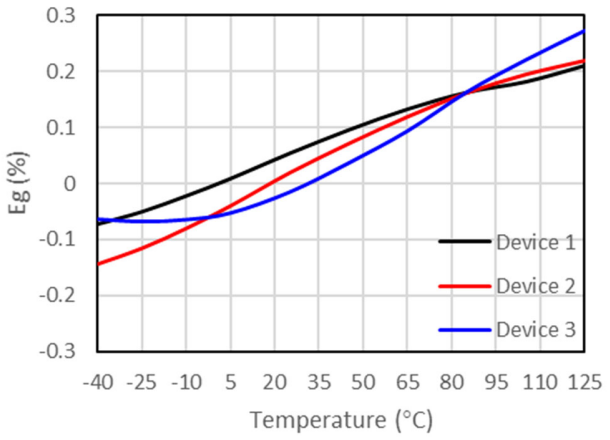


Figure 7-3. Gain vs. Temperature

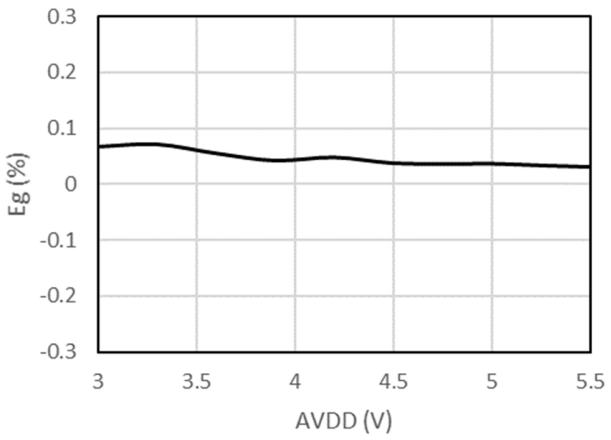


Figure 7-4. Gain Error vs. High-side Supply Voltage

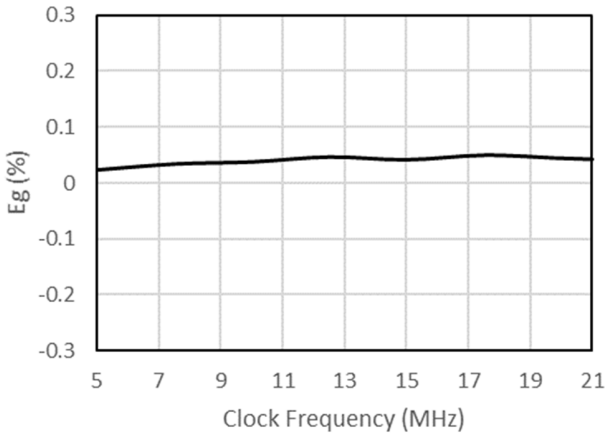


Figure 7-5. Gain Error vs. Clock Frequency

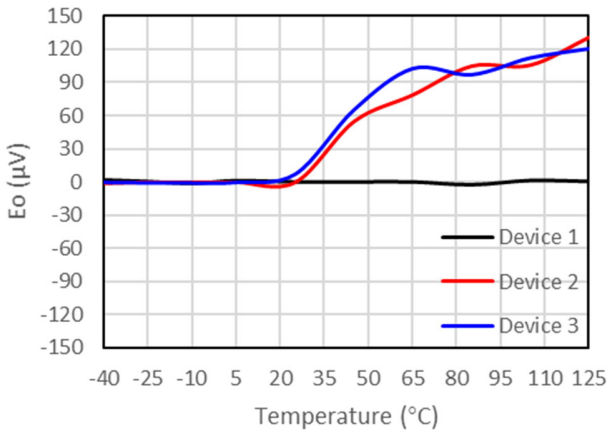


Figure 7-6. Offset vs. Temperature

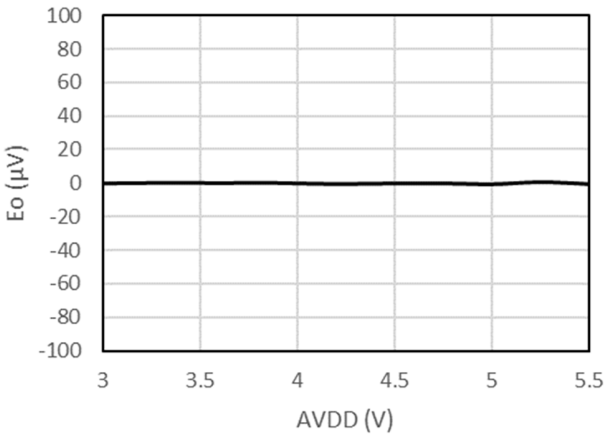


Figure 7-7. Offset Error vs. High-side Supply Voltage

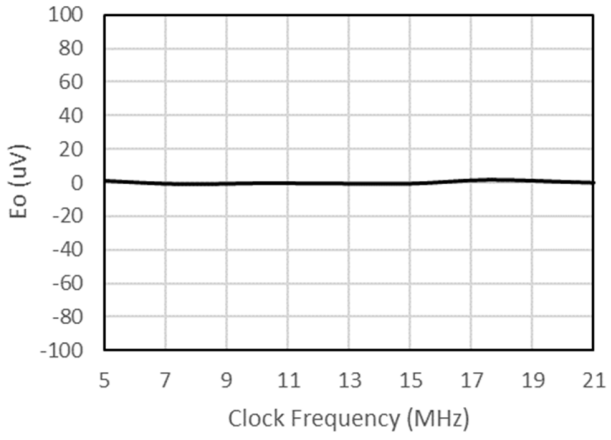


Figure 7-8. Offset Error vs. Clock Frequency

Typical Characteristics and Waveforms (Continued)

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

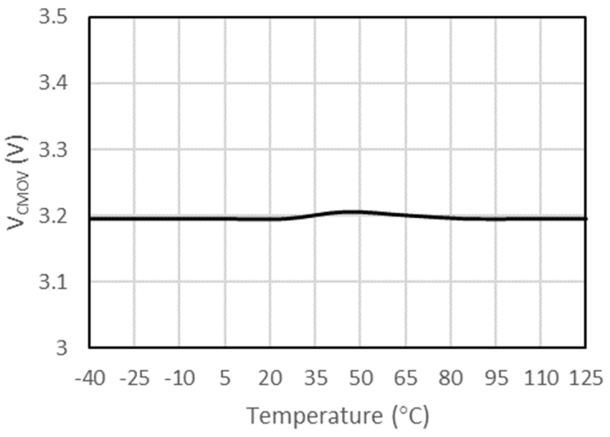


Figure 7-9. Common-mode overvoltage threshold vs. Temperature

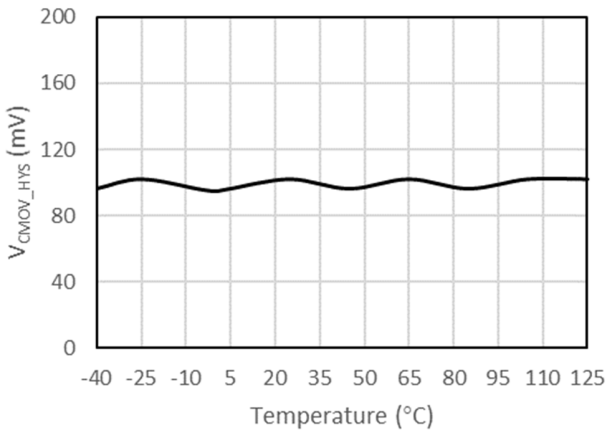


Figure 7-10. Hysteresis of common-mode over-voltage threshold vs.

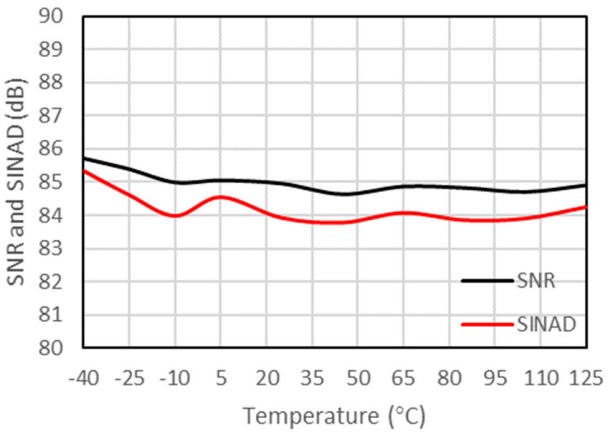


Figure 7-11. SNR & SINAD vs. Temperature

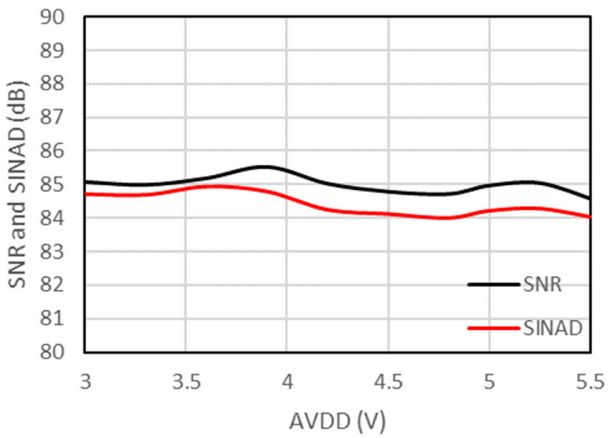


Figure 7-1. SNR & SINAD vs. High-side Supply Voltage

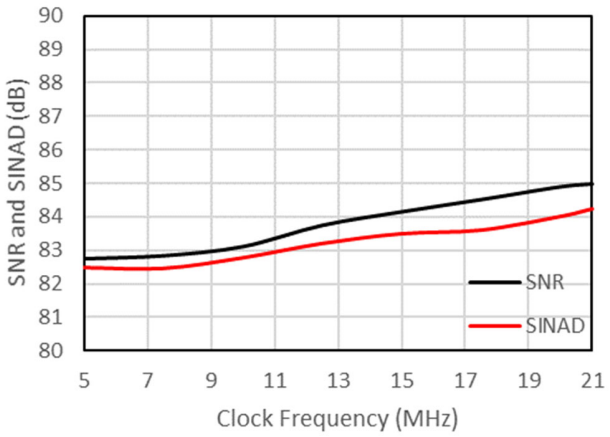


Figure 7-2. SNR & SINAD vs. Clock Frequency

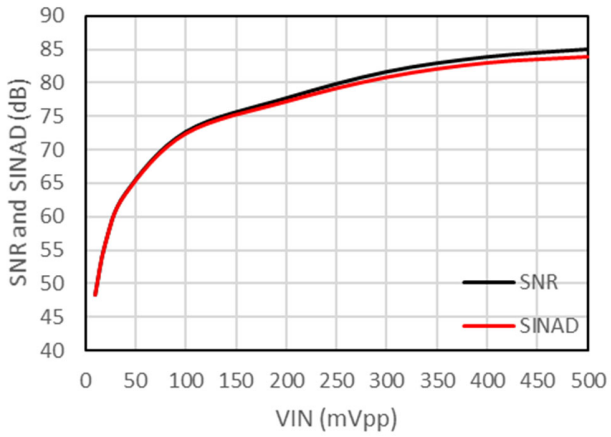


Figure 7-3. SNR & SINAD vs. Input

Typical Characteristics and Waveforms (Continued)

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

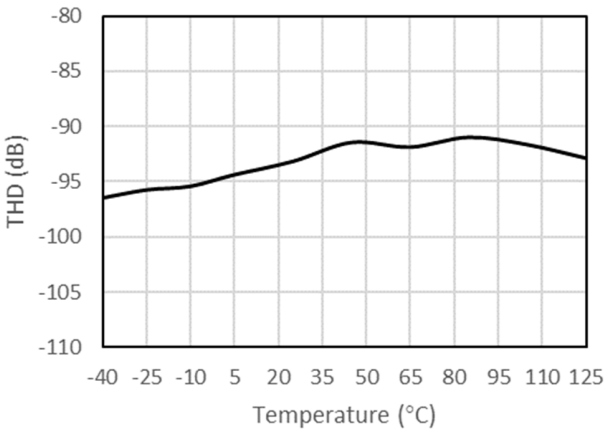


Figure 7-4. THD vs. Temperature

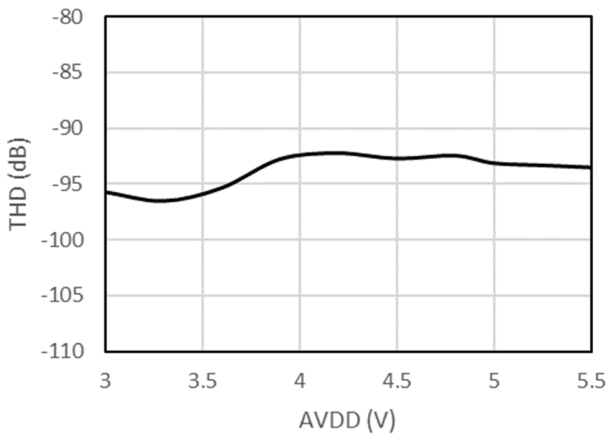


Figure 7-16. THD vs. High-side Supply Voltage

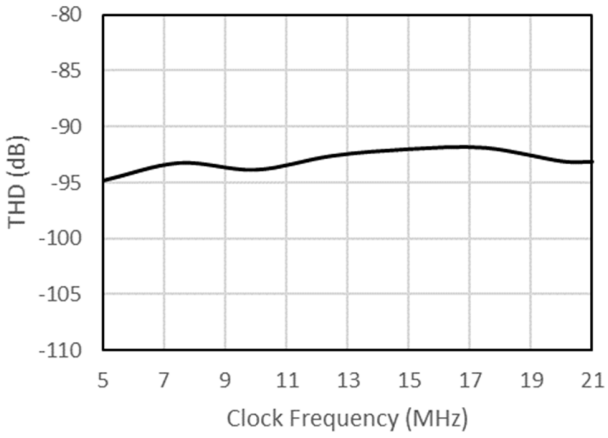


Figure 7-5. THD vs. Clock Frequency

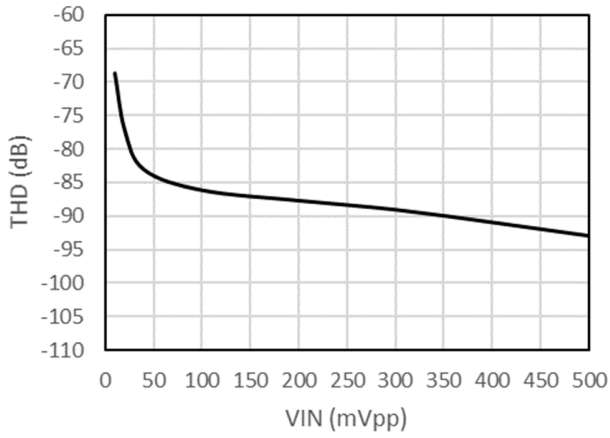


Figure 7-18. THD vs. Input

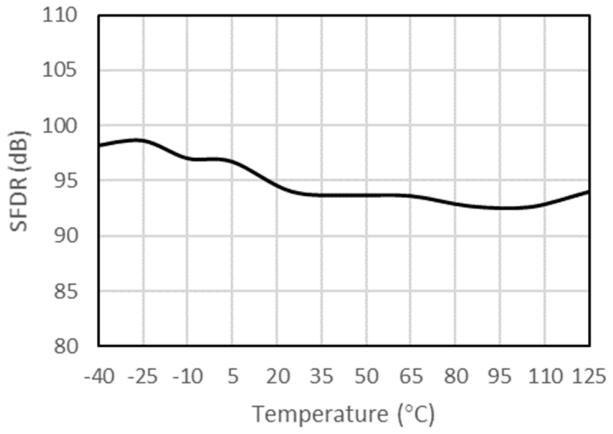


Figure 7-19. SFDR vs. Temperature

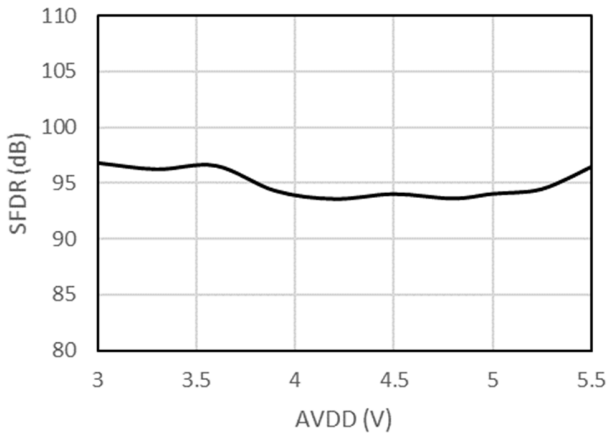


Figure 7-20. SFDR vs. High-side Supply Voltage

Typical Characteristics and Waveforms (Continued)

All minimum/maximum specs are tested over recommended operating conditions and sinc^3 filter output configured to 16 bits with OSR = 256 (unless otherwise noted). All typical values are at 25°C with CLKIN = 20 MHz, AVDD = 5 V, and DVDD = 3.3 V (unless otherwise noted).

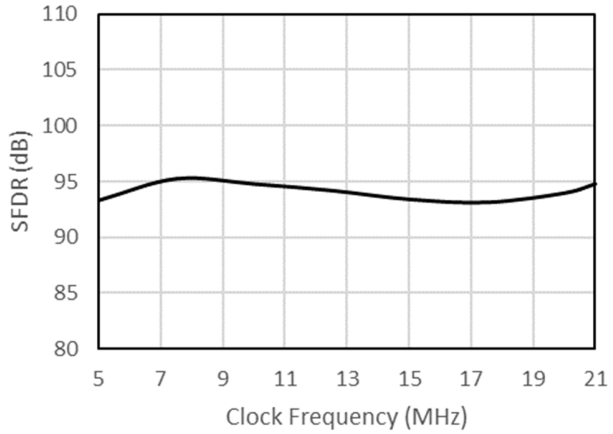


Figure 7-216. SFDR vs. Clock Frequency

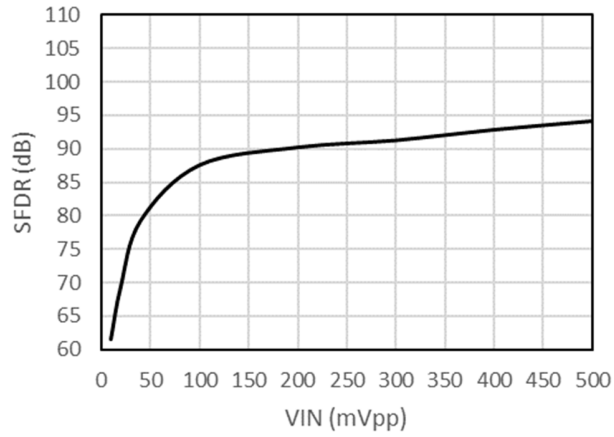


Figure 7-22. SFDR vs. Input

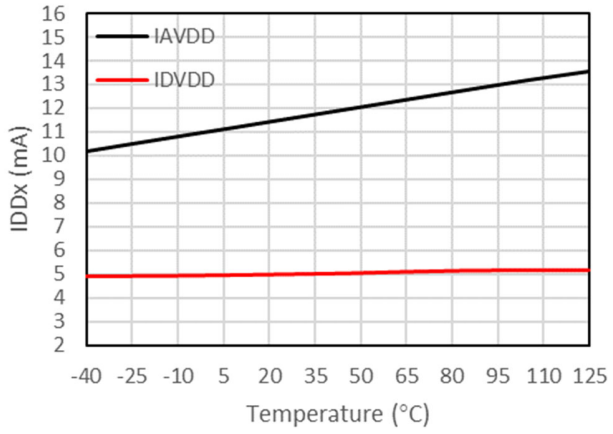


Figure 7-23. Supply Current vs. Temperature

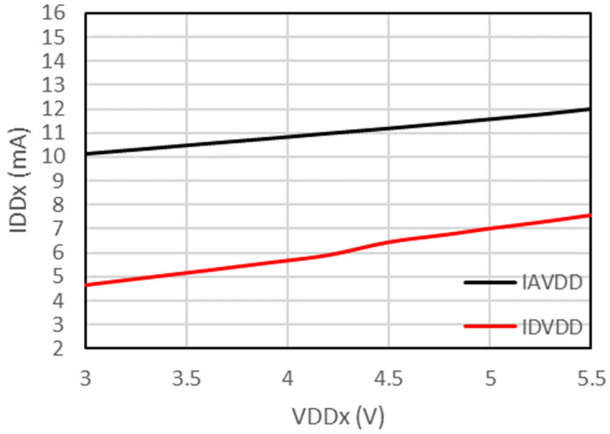


Figure 7-24. Supply Current vs. Supply Voltage

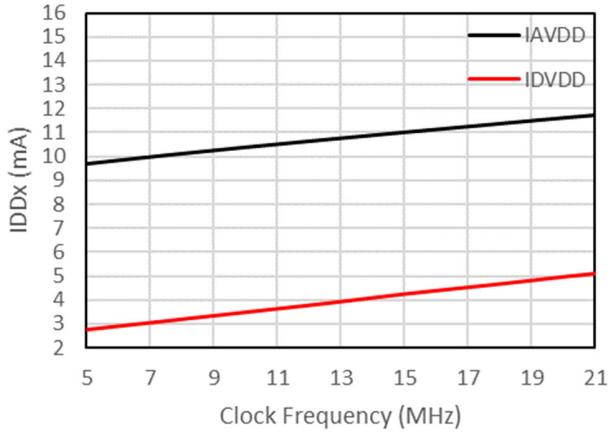


Figure 7-25. Supply Current vs. Clock Frequency

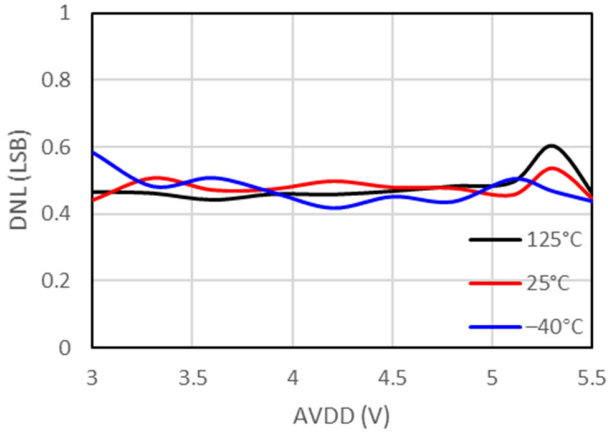


Figure 7-26. DNL vs. High-side Supply Voltage

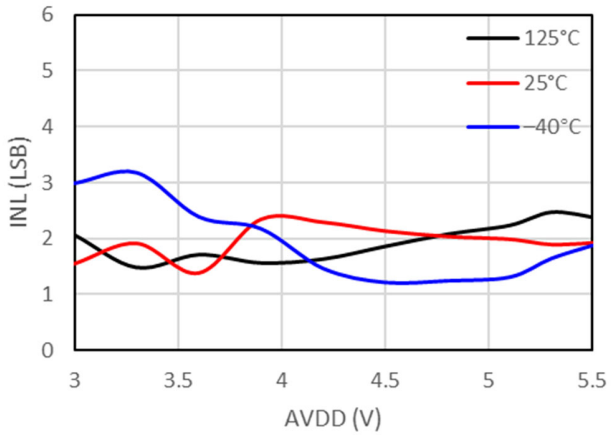


Figure 7-77 INL vs AVDD

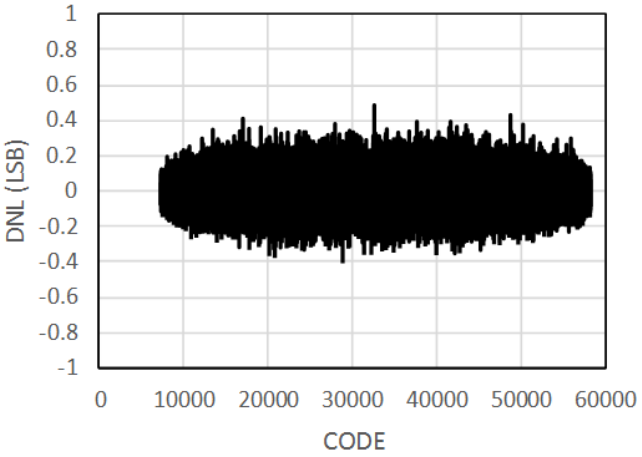


Figure 7-28 Typical DNL

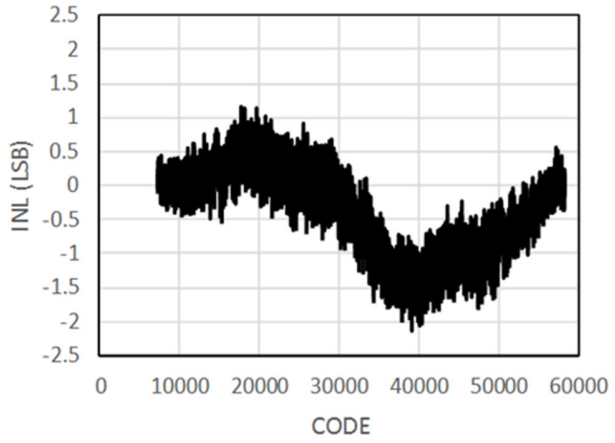


Figure 7-29 Typical INL

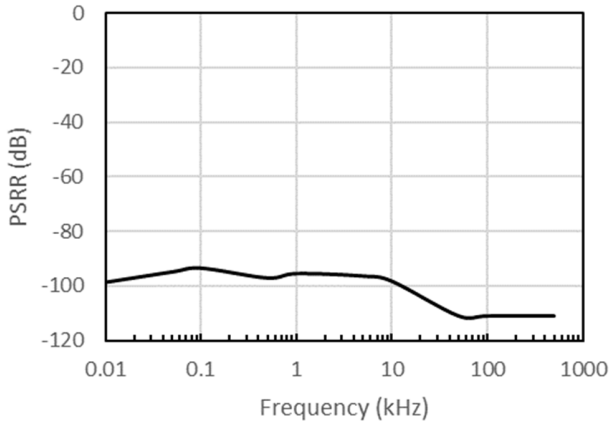


Figure 7-30 PSRR vs frequency

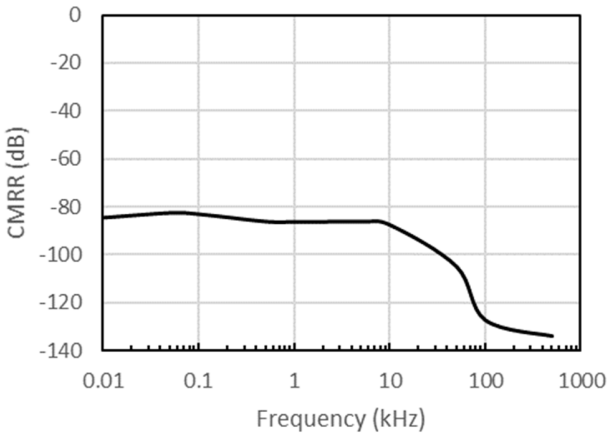


Figure 7-31 CMRR vs frequency

8 Detailed Description

8.1 Overview

The CA-IS1306x devices are series of precision isolated sigma-delta (ΣΔ) modulators optimized for shunt resistor-based current sensing and small signal measurement applications. The functional block diagram of this device is shown in Figure. This family of devices performs fully differential analog input to digital output conversion using a single-bit, second-order, switched-capacitor modulator. A single comparator within the modulator quantizes the input signal at a much higher sample rate than the bandwidth of the signal to be measured. The quantizer then presents a stream of 1s and 0s to the digital isolator driver and the driver transmit the bit stream across a SiO_2-based capacitive isolation barrier to provide up to $5kV_{RMS}$ isolation rating. The modulator is fully differential for maximum signal-to-noise ratio and minimum susceptibility to power-supply noise. On the digital output-side or low-side, the receiver demodulates the signal after advanced signal conditioning and produces the output at DOUT. The density of 1s in the DOUT bit stream output is proportional to the analog input voltage.

To synchronize the entire system operation, the device provides an external clock input CLKIN on the low-side and feeds the clock back to the high-side through digital isolation for the synchronous sigma-delta modulator operating. The input clock frequency range is from 5MHz to 21MHz, much higher than the analog input bandwidth.

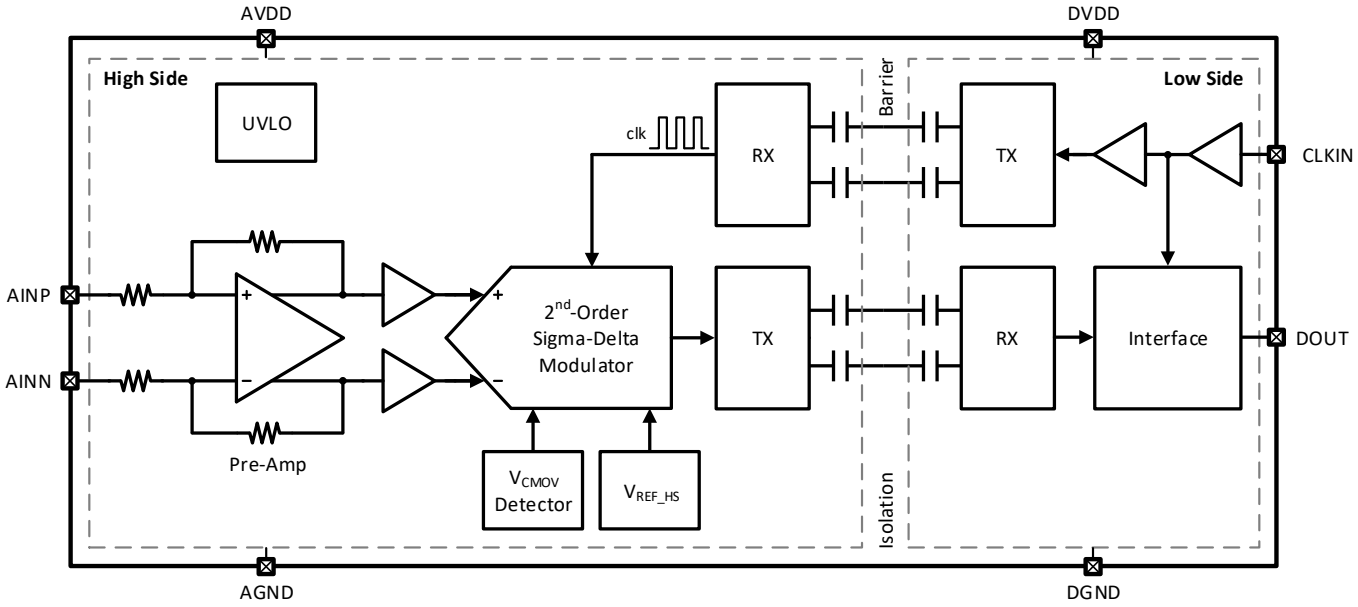


Figure 8-1. Functional Block Diagram of the CA-IS1306x

8.2 Analog Input (High-side)

The analog input of CA-IS1306x series devices utilizes a full differential preamplifier to amplify the voltage of current sense resistor R_{shunt}. The gain of the input amplifier is fixed and set by internal precision resistors. The internal fixed gain of the CA-IS1306M25 is 4x, and the corresponding full-scale input voltage range is ±250mV, the differential input impedance is 22kΩ (see the chapter 9.1.3 for more details). Considering of the lower input impedance of the CA-IS1306x devices, large gain and offset errors could be introduced when used with high-impedance signal resources. It is very important to select a reasonable current sense resistor and carefully layout the PCB.

The internal ESD protection of the CA-IS1306x can withstand (AGND–6V) to (AVDD+0.5V) absolute maximum analog input. To guarantee the long-term reliability and devices performance, the differential analog input voltage and the input common-mode voltage of CA-IS1306x should be limited within the specific range.

8.3 Signal Isolation

The CA-IS1306x family of devices utilizes Chipanalog's full differential capacitive isolation technology, as shown in Figure , that contains an ON-OFF keying (OOK) modulation scheme to transfer digital signals across the SiO_2 based isolation barrier between circuits with different power domains. The transmitter sends a high frequency carrier across the barrier to represent one digital state and sends no signal to represent the other digital state. The isolation receiver demodulates the signal and recovery input signal at output through a buffer stage, see Figure for more details. With this OOK architecture, the CA-IS1306x devices build a robust data transmission path between different power domains and support up to $5kV_{RMS}$ galvanic isolation between the analog input side and digital output side.

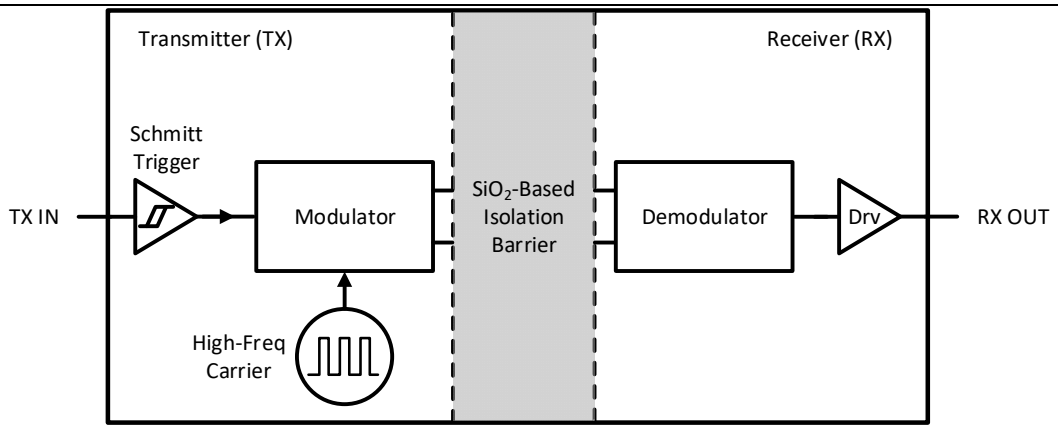


Figure 8-2. Block Diagram of the Isolation Channel

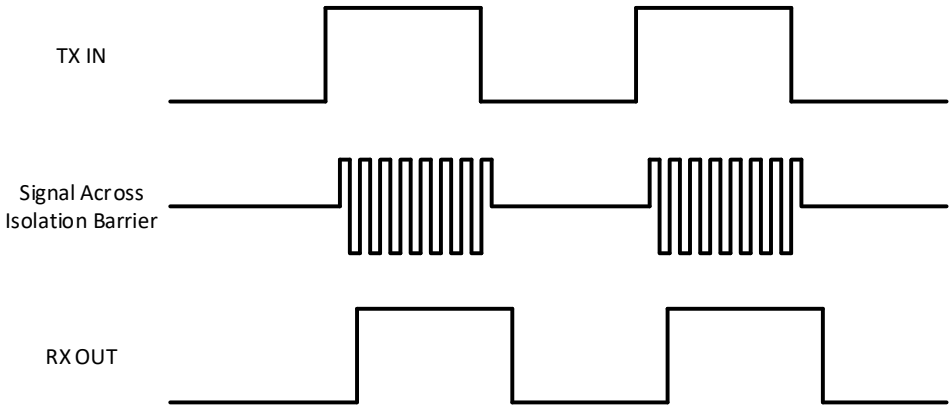


Figure 8-3. OOK Modulation

8.4 Digital Output (Low-side)

8.4.1 Bit stream output

The CA-IS1306x devices perform fully differential analog input to digital output conversion using a sigma-delta modulator. The sigma-delta modulator converts the input signal into a digital pulse train whose average duty cycle represents the digitized signal information. Figure 8-4 shows the relationship between the bit stream output vs. analog input (AINP – AINN). The analog input of 0 V ideally produces to a digital bit-stream of "1" and "0" with high 50% of the time. For the analog input voltage within full-scale input range (±320 mV), the digital output maintains a linear relationship with the analog input, and the density of 1s in the digital output bit-stream can be calculated as following equation:

$$Density|_{1s} = (V_{IN} + V_{Clipping}) / (2 \times V_{Clipping}) \quad \text{(Equation 1)}$$

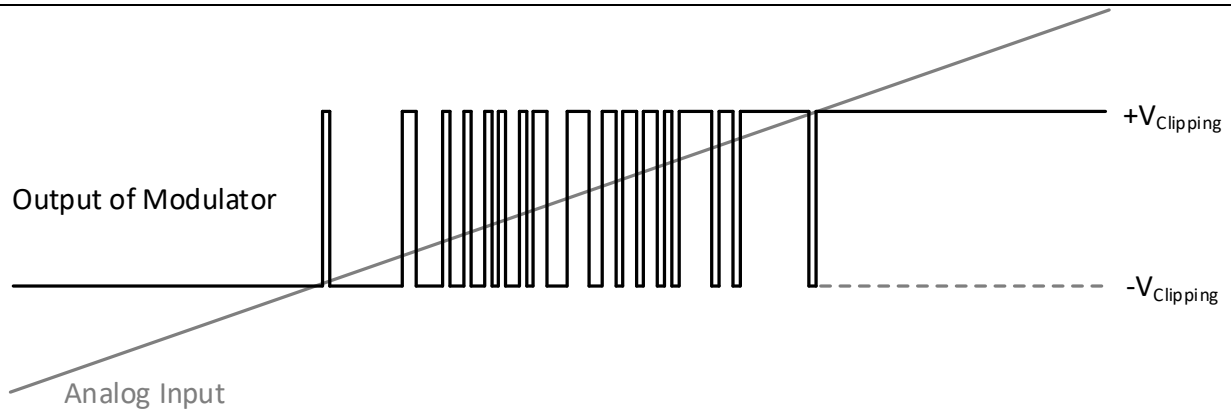


Figure 8-4. CA-IS1306x Modulator Output vs. Analog Input (AINP – AINN)

8.4.2 Over-range Output

For the analog input less than or equal to –320mV, the CA-IS1306x modulator will clip the bit-stream at "0", and generate a single "1" every 128 clocks; For the analog input greater than or equal to +320mV, the CA-IS1306x modulator will clip the bit-stream at "1", and generate a single "0" every 128 clocks, see Figure 8-5.

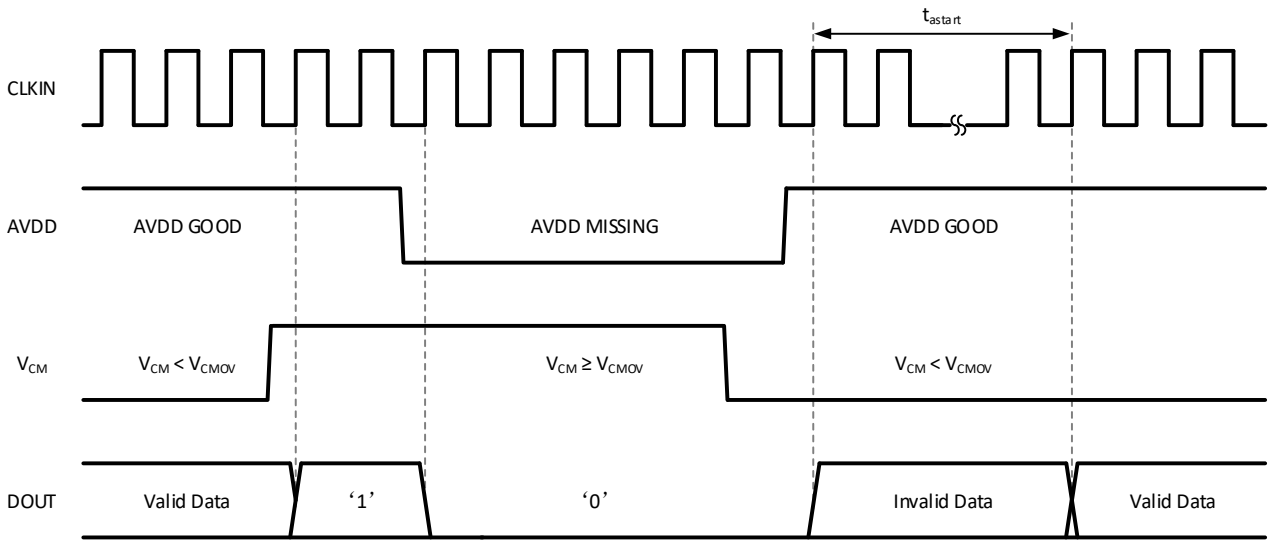


Figure 8-5. CA-IS1306x Over-range Output Waveforms

8.4.3 Fail-Safe Output

The CA-IS1306x devices feature fail-safe output indication which means the devices guarantee a logic-low on the digital output (DOUT) when the high-side power supply (AVDD) is off or loss, or a logic-high at DOUT when the common-mode input voltage V_{CM} exceeds the common-mode overvoltage threshold V_{CMOV}. When both cases occur at the same time, the priority of high side supply voltage (AVDD) loss is higher, so DOUT output will remain logic 0, see Figure 8-6 for more details. In the case of a missing high-side supply voltage AVDD, the output of Σ-Δ modulator is not defined and can cause a system fault or indeterminacy. The fail-safe output provides a fault indication for system and helps to improve system reliability. Also, in this way, differentiating between the AVDD loss and the over range input signal is possible on the system level.

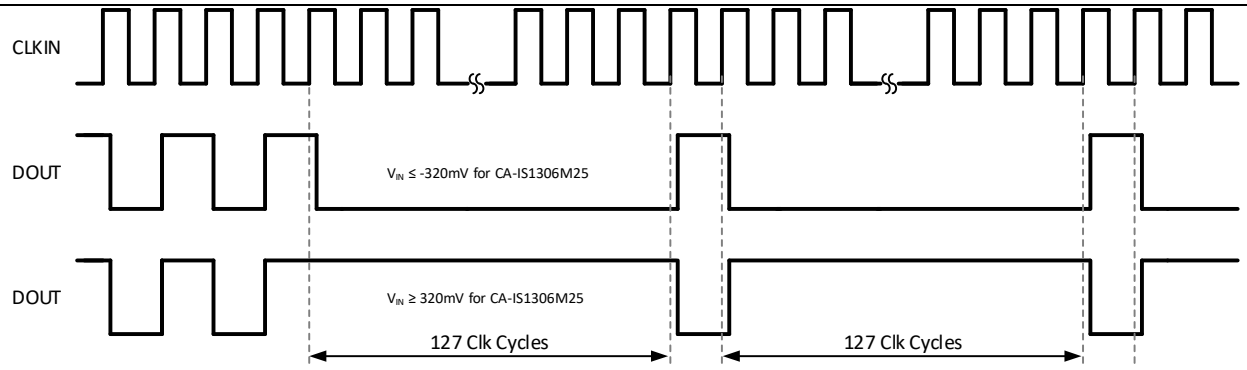


Figure 8-6. CA-IS1306x Fail-Safe Output

9 Application Information

9.1 Typical Application for Current Sense

9.1.1 Typical Application Circuit

The CA-IS1306x precision isolated sigma-delta (Σ-Δ) modulators are optimized for shunt resistor-based current sensing applications. A typical application circuit for current sense is shown in Figure, the CA-IS1306x device is used to amplify the voltage across the shunt resistor (R_{shunt}), and the internal sigma-delta modulator converts the analog signal into digital bit-stream. The isolated bit stream output is then processed by an external digital decimation filter which can be implemented by FPGA or DSP, resulting in a conversion accuracy up to 16 bits. Robust isolation coupled with up to 150kV/μs typical CMTI enables accurate small signal measurement in noisy environments, making these devices ideal for motor drives, photovoltaic inverters, uninterruptible power supplies(UPS) etc. industrial applications. Figure shows the CA-IS1306x in one motor phase current sense circuit design.

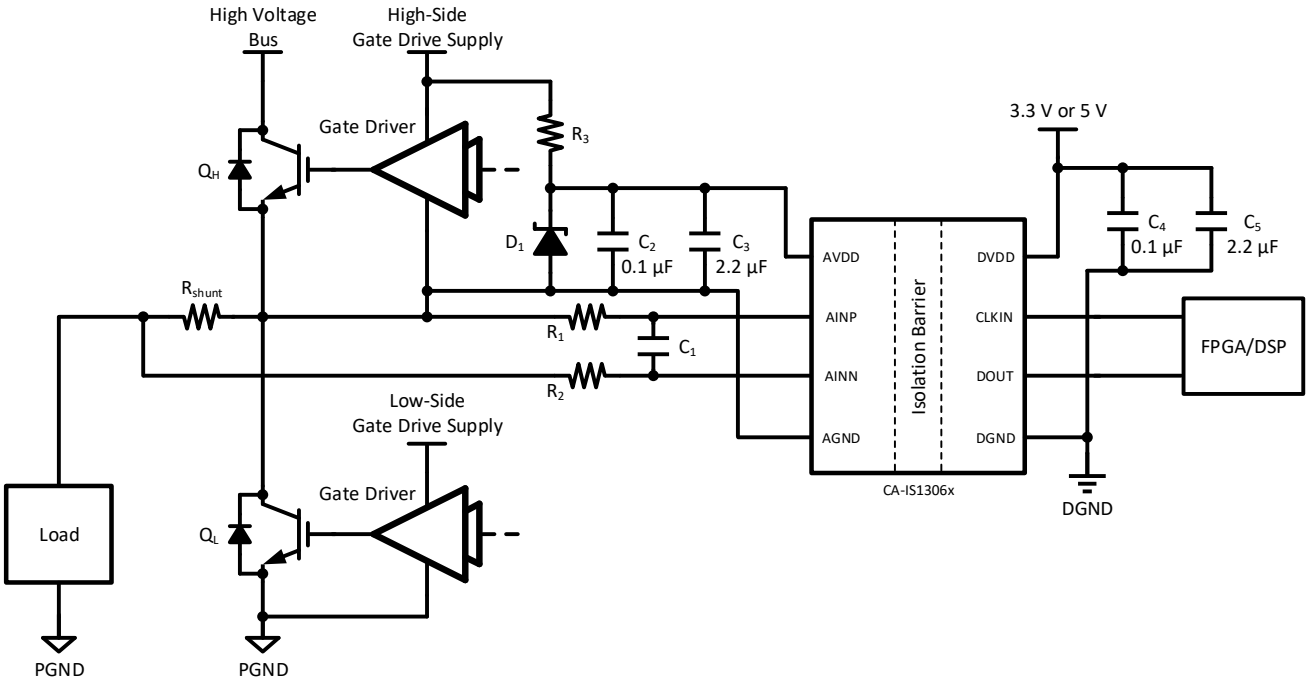


Figure 9-1. Typical Application for 1-phase Current Sensing

9.1.2 Choosing the Current Sense Resistor

The shunt resistor selection should be a trade off between power dissipation and measurement accuracy. Small value resistors minimize power dissipation, while large value resistors take advantage of the full performance input range of the sigma-delta modulator. Choose R_{shunt} based on the following criteria:

- Accuracy: a high R_{shunt} value allows lower currents to be measured more accurately. This is because offsets become less significant when the sense voltage is larger. For best performance, select R_{shunt} to provide approximately V_{FSR} (±250mV) of sense voltage for the nominal full-scale current in each application. And the voltage drop at R_{shunt} caused by the maximum current should be less than $V_{Clipping}$ (±320mV).
- Efficiency and power dissipation: at high current levels, the I^2R losses in R_{shunt} can be significant. Take this into consideration when choosing the resistor value and its power dissipation rating. Also, the sense resistor's value might drift if it is allowed to heat up excessively.

Due to the high currents that may flow through R_{shunt}, take care to eliminate solder and parasitic trace resistance from causing errors in the sense voltage. Either use a four-terminal current sense resistor or use Kelvin (force and sense) PCB layout technique. The Kelvin-sense traces should be as close as possible to the current-sense resistor's solder contact pads. If the Kelvin-sensing contact pads are spaced wider relative to the sense resistor, error is introduced from the additional trace resistance.

9.1.3 Analog Input Filter

To improve signal-to-noise performance of the CA-IS1306x's signal path, a 1st-order RC filter is recommended in front of the sigma-delta modulator, as shown in the typical application circuit Figure 9-1, selecting $R_1 = R_2 = 10\Omega$ and $C_1 = 20nF$, the input bandwidth of the analog front-end of the device can be limited within 400kHz.

9.1.4 Digital Output Filter

The CA-IS1306x modulator provides 2nd-order frequency shaping of the quantization noise resulting from the single bit quantizer. To remove the frequency shaped quantization noise, a digital decimation filter is required. For CA-IS1306x 2nd order modulator, a $sinc^3$ filter is recommended because of the low cost hardware design and better performance. A FPGA or DSP can be used to implement this filter to provide the transfer function of a $sinc^3$ filter as below.

$$H(Z) = \left[\frac{1}{DR} \frac{\left(1 - Z^{-DR}\right)}{\left(1 - Z^{-1}\right)} \right]^3 \qquad \textbf{(Equation 2)}$$

where DR is the decimation rate, it is the ratio of modulator clock frequency f_{CLKIN} and throughput rate of the $sinc^3$ filter f_{DATA}, which is also called oversampling rate (OSR).

$$\boldsymbol{DR = OSR = f_{CLKIN}/f_{DATA}} \qquad \textbf{(Equation 3)}$$

The output data width is shown in below equation.

$$\boldsymbol{Data\ Width = 3 \times \log_2 DR} \qquad \textbf{(Equation 4)}$$

All of the characterization in section of Electrical Characteristics is done with a $sinc^3$ filter with an oversampling ratio(OSR)

of 256 and an output word width of 16 bits.

The characteristics of the sinc^3 filter are summarized in Table 9-1. As the decimation rate increased, the output data width from sinc^3 filter increased as well, while the throughput rate decreased, resulting higher SNR performance. Thus, designers can trade off between data rate and conversion accuracy based on the application requirements.

Table 9-1. Characteristics of sinc^3 Filter at 20MHz f_{CLKIN}

Decimation Rate (DR)	f_{DATA} (kHz)	Output Data Width (Bits)	Filter Response (kHz)
32	625	15	163.7
64	312.5	18	81.8
128	156.2	21	40.9
256	78.1	24	20.4
512	39.1	27	10.2

9.2 Voltage Measurement

The CA-IS1306x current sense amplifiers, along with a voltage divider, can be used as an isolated voltage measurement solution, see Figure 9-2 typical application circuit. The resistors of R_{41}, R_{42}, R_{51}, R_{52}, R_{61} and R_{62} are the internal resistors of the CA-IS1306x device, where R_{41}, R_{42}, R_{51},and R_{52} are used to setup the amplifier gain, R_{41} = R_{42} = 12.5 kΩ, R_{51} = R_{52} = 50 kΩ; R_{61} and R_{62} are used for the common-mode voltage detector, R_{61} = R_{62} = 100 kΩ. The voltage-divider (R_{21}+R_{11} and R_{31}) reduces the input voltage from the power supply bus voltage to ±250mV to match the input range of the CA-IS1306x. Thus, for the high-voltage power supply bus, (R_{21}+R_{11}) >>R_{31}.

The bias current I_{INP} passing through the voltage sense resistor R_{31} will cause significant offset error. To reduce the gain error and offset error, select R_{31} as small as possible. However, to limit the current consumption of the voltage-divider, choosing large resistance values for R_{21}+R_{11} and R_{31} will minimize overall power consumption. Designers need to balance the choice of resistance.

In order to cancel out the offset error introduced by the bias current I_{INP} flowing through R_{31}, the resistor R_{32} is added at VINN input. As the error compensating resistor, the ideal R_{32} should be the parallel resistance of (R_{21}+R_{11})//R_{31}, see below R_{32} calculation equation,

$$R_{32} = \frac{R_{31}x(R_{21} + R_{11})}{R_{31} + R_{21} + R_{11}} \cong R_{31}\,, \quad (R_{11} + R_{21} \gg R_{31})$$

Adding R_{32} can remove the offset error caused by I_{INP}, but there will be an expected difference between the modulator's differential input voltage (AINP – AINN) and the voltage drop on R_{31} given by the resistor divider. This discrepancy can be expressed as a gain error, as shown in below equation,

$$G_{ERROR} = \frac{R_{31}}{R_{31} + R_{41}}$$

Choosing appropriate R_{31} to balance gain error and power consumption, combine with compensating resistor R_{32}, the voltage measurement performance shown in Figure 9-2 typical application circuit is acceptable for most applications.

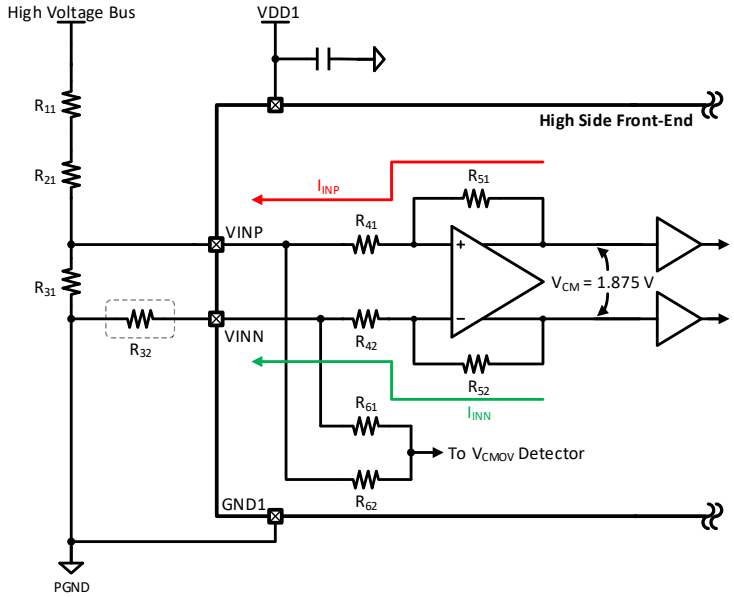


Figure 9-2. Typical Application Circuit for Voltage-Measurement

9.3 Power supply and PCB layout

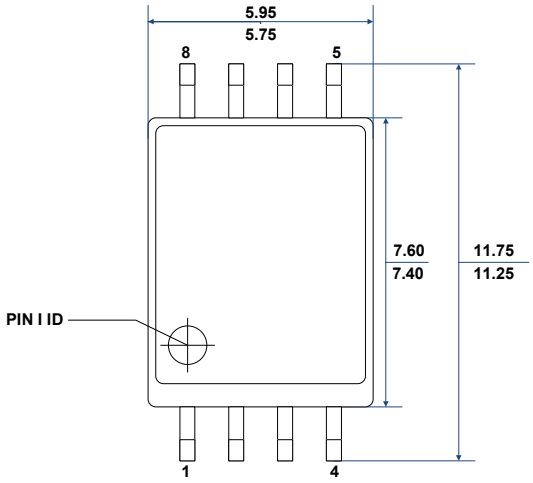
The CA-IS1306x devices require dual power supply to provide supply for analog input-side and digital output-side in the different voltage domain. The supply range of both AVDD and DVDD is 3.0V to 5.5V. To reduce system-level cost, the power supply of AVDD can be derived from the system main power supply by using a Zener diode(D_1 in Figure 9-1) to limit the voltage to 5V or 3.3V (±10%). Alternatively a low-cost low-drop regulator (LDO) can be used to produce a stable supply voltage level for AVDD and minimize noise on the power-supply as well.

Good layout technique optimizes performance by decreasing the amount of stray capacitance at the high-side, current-sense-amplifier, common-mode inputs etc. Capacitive decoupling across the supply voltage AVDD to AGND(C_2), DVDD to DGND(C_4) of low-ESR 0.1µF is recommended as shown in Figure 9-1. If better filtering is required, an extra bulk capacitor (2.2µF to 10µF) can be added(C_3, C_5). In current sense applications, since the CA-IS1306x devices feature ultra-low input offset voltage, board leakage and thermocouple effects can easily introduce errors in the input offset voltage readings when used with high-impedance signal sources. In order to dissipate sense-resistor heat from large sense currents, solder the AINP and the AINN pins to large copper traces. Keep the part away from other heat-generating devices. For accurate measurement of V_{shunt}, the Kelvin method is recommended. For noisy digital environments, keep digital signals far away from the sensitive analog inputs. The use of a multilayer PCB with separate ground and power-supply planes is recommended.

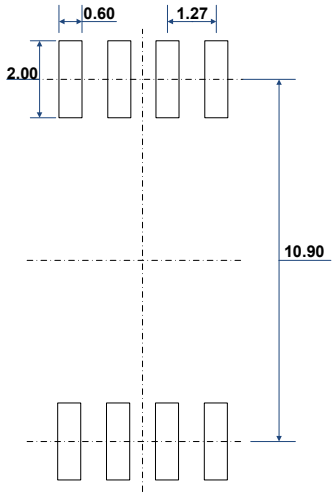
10 Package Information

8-Pin Wide Body SOIC Package

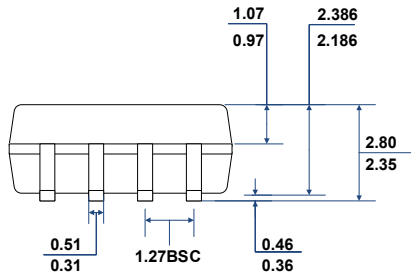
The figure below illustrates the package details and the recommended land patternfor the CA-IS1306x isolated sigma-delta modulator in 8-pin wide-body SOIC package. The values for the dimensions are shown in millimeters.



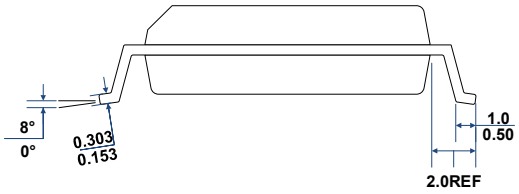
TOP VIEW



RECOMMENDED LAND PATTERN



FRONT VIEW



LEFT-SIDE VIEW

11 Soldering Temperature (reflow) Profile

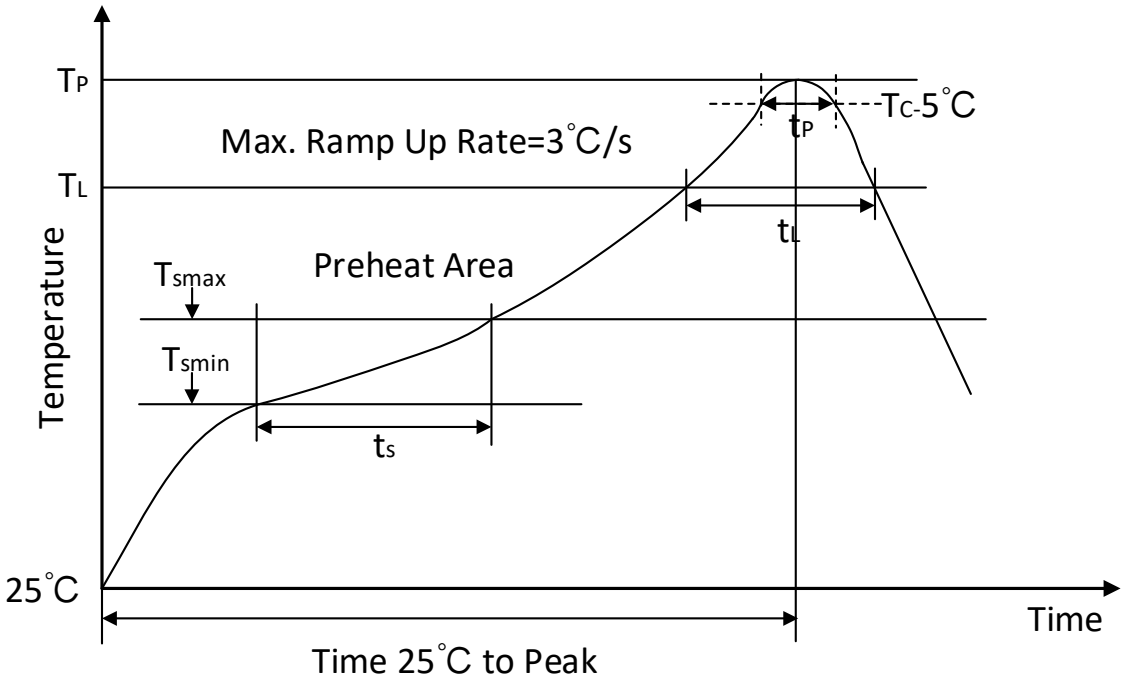


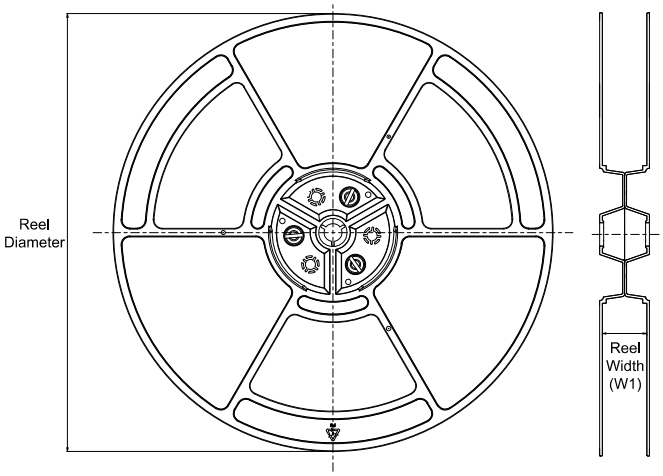
Figure 11-1. Soldering Temperature (reflow) Profile

Table 11-1. Soldering Temperature Parameter

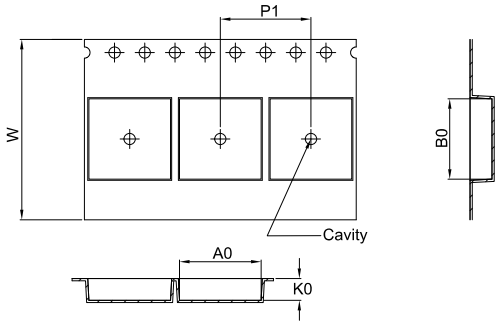
Profile Feature	Pb-Free Assembly
Average ramp-up rate(217℃ to Peak)	3℃ /second max
Time of Preheat temp(from 150℃ to 200℃)	60-120 second
Time to be maintained above 217℃	60-150 second
Peak temperature	260 +5/-0 ℃
Time within 5℃ of actual peak temp	30 second
Ramp-down rate	6 ℃ /second max.
Time from 25℃ to peak temp	8 minutes max

12 Tape and Reel Information

REEL DIMENSIONS

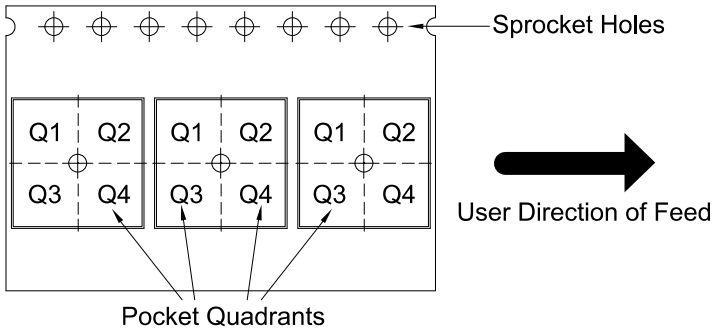


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CA-IS1306M25G	SOIC	G	8	1000	330	16.4	12.05	6.15	3.3	16.0	16.0	Q1
CA-IS1306AM25W	SOIC	W	16	1000	330	16.4	10.9	10.7	3.2	12.0	16.0	Q1
CA-IS1306M25W	SOIC	W	16	1000	330	16.4	10.9	10.7	3.2	12.0	16.0	Q1

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